

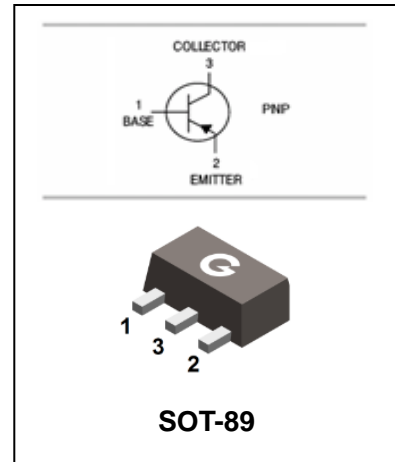
PNP Silicon Planar High Voltage Transistor

FCX558

FEATURES

- Complementary type: FCX458
- RoHS compliant with Halogen-free

HF



ORDERING INFORMATION

Type No.	Marking	Package Code
FCX558	P58	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{CM}	Peak Pulse Current	-500	mA
I_C	Collector Current -Continuous	-200	mA
P_D	Power Dissipation	1	W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}, I_{CES}	$V_{CB}=-320V; V_{CES}=320V$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-10V, I_C=-1mA$ $V_{CE}=-10V, I_C=-50mA$ $V_{CE}=-10V, I_C=-100mA$	100 100 15		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-20mA, I_B=-2mA$ $I_C=-50A, I_B=-6mA$			-0.2 -0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50A, I_B=-5mA$			-0.9	V
Base-emitter Turn-on Voltage	$V_{BE(on)}$	$I_C=-50A, V_{CE}=-10V$			-0.9	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA,$ $f=100MHz$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			10	pF
Switching times	t_{on} t_{off}	$I_C=-50mA, V_C=-100V$ $I_{B1}=-5mA, I_{B2}=-10mA$		95 Typical 1600 Typical		ns ns

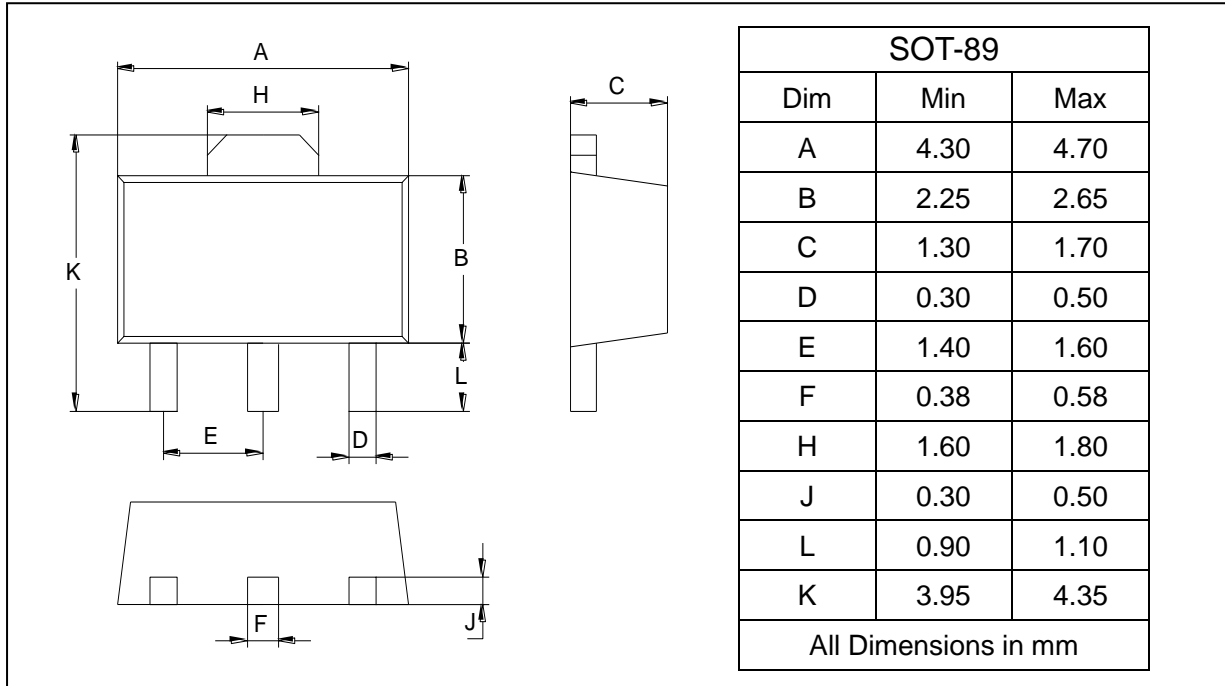
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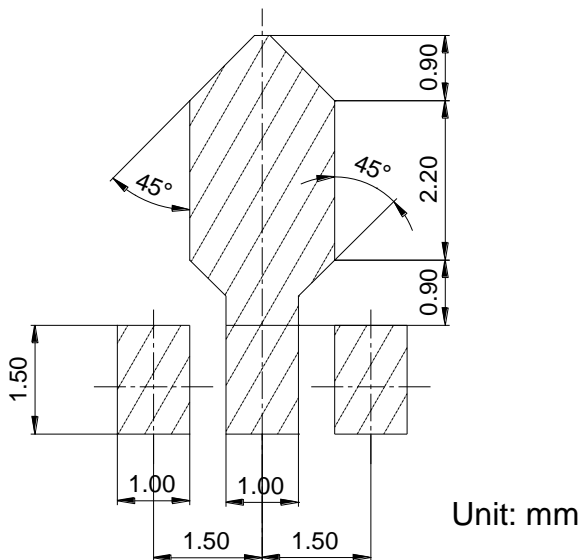
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
FCX558	SOT-89	1000 pcs / Tape & Reel